



Digitale Interoperabilität in kollaborativen
Wertschöpfungsnetzwerken der Industrie 4.0

Submodel Semiconductor Datasheet - Final Presentation of Results

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Ein Projekt gefördert vom



Durchgeführt von



Agenda

- About Interopera – Facts & Figures
- About the Semiconductor Datasheet Project – Facts & Figures
- Ferdinand-Steinbeis-Institut – Our Expertise
- Use Case “Semiconductor Datasheet“ - Scope
- Project Results – The Asset Administration Shell for Power Semiconductors
- Discussion



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About Interopera – Facts & Figures

About Interopera – Facts & Figures



Goal: The development of 50 submodels of the Asset Administration Shell (AAS) across the Referenzarchitekturmodell Industrie 4.0 (RAMI 4.0) for a variety of business processes.

Duration: 03/2021 – 12/2023

Consortium:

- Steinbeis Europa Zentrum,
- Fraunhofer-Institut für Produktionstechnik und Automatisierung IPA,
- Standardization Council Industrie 4.0 des VDE DKE in Kooperation mit der Plattform Industrie 4.0 und ihrer Partner ZVEI, VDMA, und Bitkom

Funding:

Funded by the Bundesministerium für Wirtschaft und Klimaschutz (BMWK)

Interopera - Approach



Separation of method/AAS experts and users

- 1.** Step: Open Call and selection of Use Cases
- 2.** Step: Open Call and selection of qualified AAS expert
- 3.** Step: Constitute project teams (open for everyone to join)
- 4.** Step: Implementation: Develop an AAS-Template for the Use Case (using eClass)



About the Semiconductor Datasheet Project – Facts & Figures

About the Semiconductor Datasheet Project – Facts & Figures



Duration: 21.11.2022 - 21.06.2023

Meetings: 2 on premise meetings in Stuttgart and 3 online meetings

Focus: Properties of Power Semiconductors

Involved Companies: PE-Systems, Bosch, Dynex Semiconductors, Fronius, Hitachi Energy, Infineon, Rohm Semiconductors, Silicon Austria, Semikron-Danfoss, SwissSem, Wolfspeed, Ferdinand-Steinbeis-Institut



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Ferdinand-Steinbeis-Institute – Our Expertise

Steinbeis Stiftung - Overview

Transfer of knowledge into companies and society

Steinbeis Transferzentren

- About 1.100 companies
- Focus on consulting, qualification, etc.
- about 5.000 employees¹
- Turnover ca.160 Mio. €¹

Steinbeis Universiy

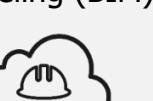
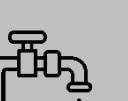
- Bachelor, Master, PhD-Programs
- about 6.000 students
- Technology & Engineering, Leadership & Management, Business & Economics

Ferdinand Steinbeis Institute

- Research Institute about the transformation of business and society
- Principle of dual scientific research
- Founded in 2015
- About 30 employees
- Located in Stuttgart & Heilbronn
- Industrial IoT & Digital Twin Consortium



Building digital Twins within Business Ecosystems (Selected projects)

Trade	Customer Services	Restaurants / Hotels	Risk mitigation	Milk	Craft
					
Additive Manufacturing	Additive Manufacturing 2	Industry	Mobility	Building Information Modeling (BIM)	Cooling and lubrication
					
Agriculture	Scheduling	Industrial Service	Smart Living	Care	Production - PPMP
					
Sustainable Logistics	Wood	Pay per Part	Smart Water	Eating out	Harbour
					
Digital Plattform Transport	Craft	Intralogistic			
					

 gefördert
 abgeschlossen
 laufend



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Use Case “Semiconductor Datasheet“ - Scope

Technical product data sheets

Example 1 – Hitachi Energy



Data sheet TS-MD/342/21 Jun 22

5SED 0890T2260

60Pak rectifier diode module

- $V_{RRM} = 2200 \text{ V}$
- $I_{FVAm} = 889 \text{ A}$
- $I_{FSM} = 22000 \text{ A}$
- $V_{TO} = 0.782 \text{ V}$
- $r_T = 0.209 \text{ m}\Omega$
- Insulated baseplate by AlN ceramic
- Precision pressure contacts for high reliability
- Industry standard housing



Maximum rated values¹⁾

Parameter	Symbol	Conditions	Min.	Max.	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_j = -40 \dots 160^\circ\text{C}$	2200		V

Source: ABB Library - Halbleiter

Example 2 – Swiss Sem



DATASHEET
SISD0750ED120i20
ED-Type phase leg IGBT module



$V_{CE} = 1200 \text{ V}$
 $I_C = 2 \times 750 \text{ A}$

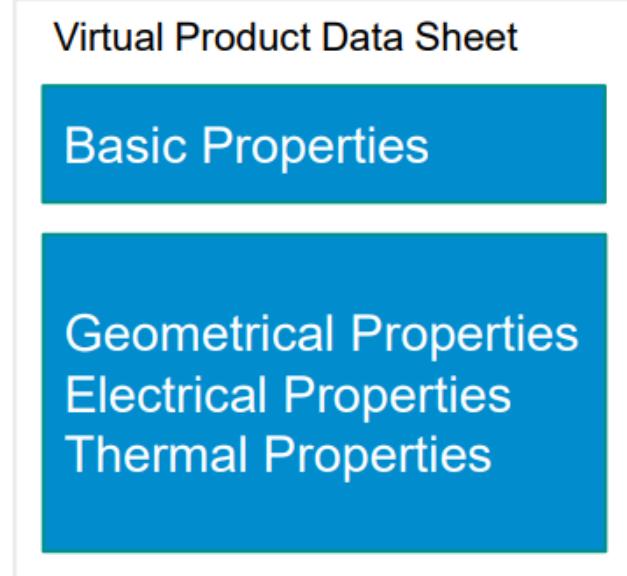
- i20 ultra-low loss fine pattern Trench IGBT chipset
- Baseplate isolation with efficient Al₂O₃ ceramic
- Cu baseplate for low thermal resistance
- Industry standard package

Maximum ratings¹⁾

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
Collector-emitter voltage	V_{CES}	$V_{ce} = 0 \text{ V}, T_c = 25^\circ\text{C}$		1200	V
DC collector current	I_C	$T_c = 110^\circ\text{C}, T_e = 175^\circ\text{C}$	750		A

Source: 750A - SwissSEM (CH) (swiss-sem.com)

Use Case im Detail



Objectives:

Comparability of semiconductors
(from different manufacturers) for the
customers

- Assessment of relevant properties
- Transferring properties into AAS
- Assessment of additional requirements for the AAS features and AAS editor

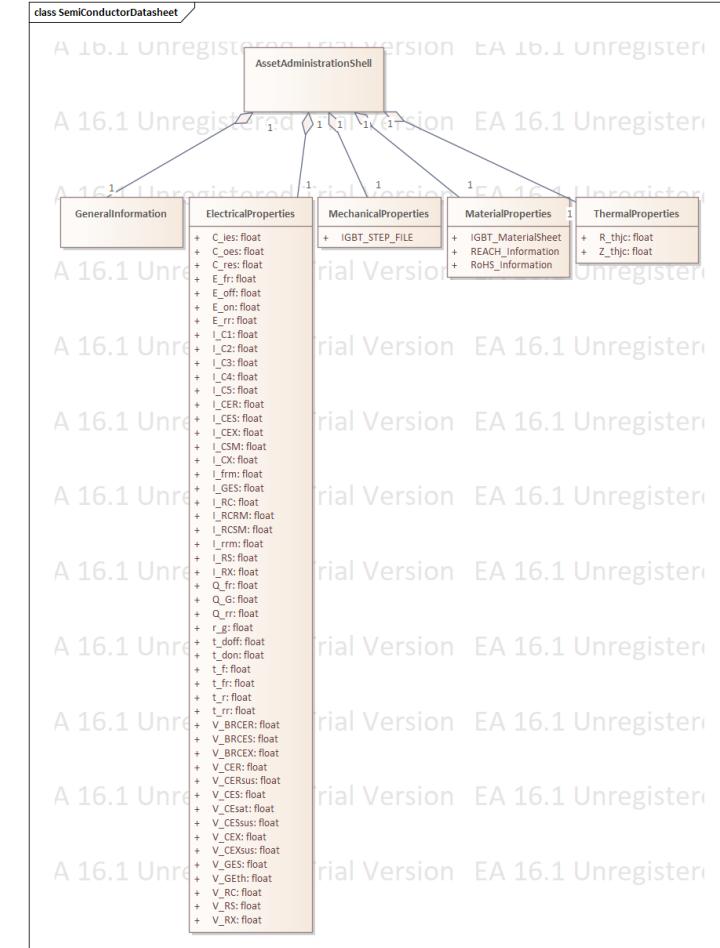
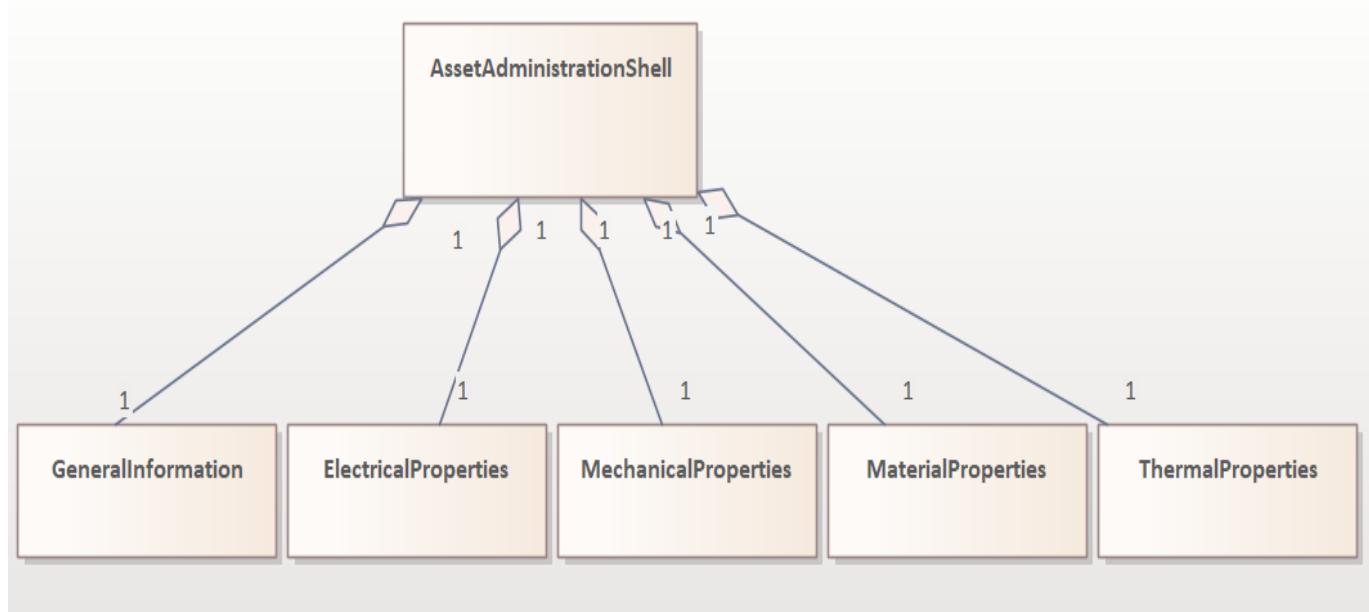




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Project Results – The Asset Administration Shell for Power Semiconductors

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Live Demonstration / Access the AAS-Template



Live Demo



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Discussion



Danke für Ihr Kommen!

www.interopera.de

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